



New Product

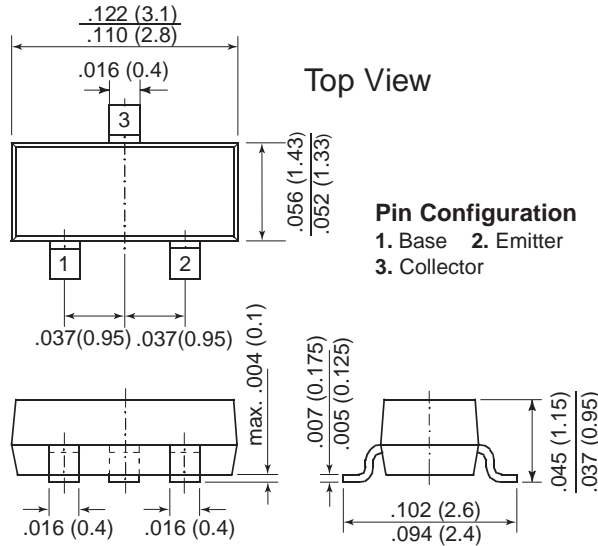
BCW60 Series

Vishay Semiconductors  
formerly General Semiconductor

## Small Signal Transistors (NPN)

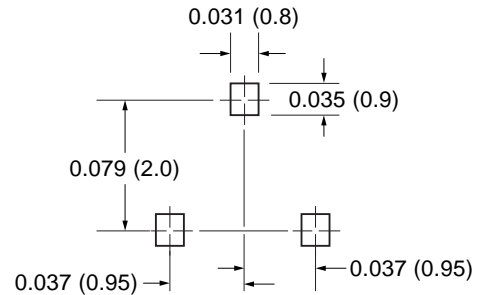


TO-236AB (SOT-23)



Dimensions in inches and (millimeters)

### Mounting Pad Layout



### Mechanical Data

**Case:** SOT-23 Plastic Package

**Weight:** approx. 0.008g

**Marking** BCW60A = AA

**Code:** BCW60B = AB

BCW60C = AC

BCW60D = AD

**Packaging Codes/Options:**

E8/10K per 13" reel (8mm tape), 30K/box

E9/3K per 7" reel (8mm tape), 30K/box

### Features

- NPN Silicon Epitaxial Planar Transistors
- Suited for low level, low noise, low frequency applications in hybrid circuits.
- Low Current, Low Voltage.
- As complementary types, BCW61 Series PNP transistors are recommended.

### Maximum Ratings & Thermal Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Value	Unit
Collector-Emitter Voltage ( $V_{BE}=0$ )	$V_{CES}$	32	V
Collector-Emitter Voltage	$V_{CEO}$	32	V
Emitter-Base Voltage	$V_{EBO}$	5.0	V
Collector Current (DC)	$I_C$	100	mA
Peak Collector Current	$I_{CM}$	200	mA
Base Current (DC)	$I_B$	50	mA
Power Dissipation	$P_{tot}$	250	mW
Maximum Junction Temperature	$T_j$	150	°C
Storage Temperature Range	$T_s$	-65 to +150	°C
Thermal Resistance Junction to Ambient Air	$R_{\theta JA}$	500 <sup>(1)</sup>	°C/W

**Note:**

(1) Mounted on FR-4 printed-circuit board.

## Electrical Characteristics Ratings at 25°C ambient temperature unless otherwise specified.

Parameter	Symbol	Min.	TYP.	Max.	Unit
DC Current Gain					
at $V_{CE} = 5V$ , $I_C = 10 \mu A$	BCW60A	$h_{FE}$	–	–	–
at $V_{CE} = 5V$ , $I_C = 10 \mu A$	BCW60B	$h_{FE}$	20	–	–
at $V_{CE} = 5V$ , $I_C = 10 \mu A$	BCW60C	$h_{FE}$	40	–	–
at $V_{CE} = 5V$ , $I_C = 10 \mu A$	BCW60D	$h_{FE}$	100	–	–
at $V_{CE} = 5V$ , $I_C = 2 mA$	BCW60A	$h_{FE}$	120	–	220
at $V_{CE} = 5V$ , $I_C = 2 mA$	BCW60B	$h_{FE}$	180	–	310
at $V_{CE} = 5V$ , $I_C = 2 mA$	BCW60C	$h_{FE}$	250	–	460
at $V_{CE} = 5V$ , $I_C = 2 mA$	BCW60D	$h_{FE}$	380	–	630
at $V_{CE} = 1V$ , $I_C = 50 mA$	BCW60A	$h_{FE}$	50	–	–
at $V_{CE} = 1V$ , $I_C = 50 mA$	BCW60B	$h_{FE}$	70	–	–
at $V_{CE} = 1V$ , $I_C = 50 mA$	BCW60C	$h_{FE}$	90	–	–
at $V_{CE} = 1V$ , $I_C = 50 mA$	BCW60D	$h_{FE}$	100	–	–
Collector-Emitter Saturation Voltage					
at $I_C = 10 mA$ , $I_B = 0.25 mA$	$V_{CEsat}$	50	–	350	mV
at $I_C = 50 mA$ , $I_B = 1.25 mA$	$V_{CEsat}$	100	–	550	mV
Base-Emitter Saturation Voltage					
at $I_C = 10 mA$ , $I_B = 0.25 mA$	$V_{BEsat}$	600	–	850	mV
at $I_C = 50 mA$ , $I_B = 1.25 mA$	$V_{BEsat}$	700	–	1050	mV
Base-Emitter Voltage					
at $V_{CE} = 5V$ , $I_C = 2 mA$	$V_{BE}$	550	650	750	mV
at $V_{CE} = 5V$ , $I_C = 10 \mu A$	$V_{BE}$	–	520	–	mV
at $V_{CE} = 1V$ , $I_C = 50 mA$	$V_{BE}$	–	780	–	mV
Collector-Emitter Cut-off Current					
at $V_{CE} = 32V$ , $V_{BE} = 0V$	$I_{CES}$	–	–	20	nA
at $V_{CE} = 32V$ , $V_{BE} = 0V$ , $T_A = 150^\circ C$		–	–	20	$\mu A$
Emitter-Base Cut-off Current					
at $V_{EB} = 4V$ , $I_C = 0$	$I_{EBO}$	–	–	20	nA
Gain-Bandwidth Product					
at $V_{CE} = 5V$ , $I_C = 10 mA$ , $f = 100 MHz$	$f_T$	100	250	–	MHz
Collector-Base Capacitance					
at $V_{CB} = 10V$ , $f = 1 MHz$ , $I_E = 0$	$C_{CB0}$	–	2.5	–	pF
Emitter-Base Capacitance					
at $V_{EB} = 0.5V$ , $f = 1 MHz$ , $I_C = 0$	$C_{EB0}$	–	8	–	pF
Noise Figure					
at $V_{CE} = 5V$ , $I_C = 200 \mu A$ , $R_S = 2 k\Omega$ , $f = 1 kHz$ , $B = 200 Hz$	$F$	–	2	6	dB
Small Signal Current Gain					
at $V_{CE} = 5V$ , $I_C = 2 mA$ , $f = 1.0 kHz$	BCW60A	$h_{fe}$	–	200	
	BCW60B	$h_{fe}$	–	260	
	BCW60C	$h_{fe}$	–	330	
	BCW60D	$h_{fe}$	–	520	
Turn-on Time at $R_L = 990\Omega$ (see fig. 1)					
$V_{CC} = 10V$ , $I_C = 10 mA$ , $I_{B(on)} = -I_{B(off)} = 1 mA$	$t_{on}$	–	85	150	ns
Turn-off Time at $R_L = 990\Omega$ (see fig. 1)					
$V_{CC} = 10V$ , $I_C = 10 mA$ , $I_{B(on)} = -I_{B(off)} = 1 mA$	$t_{off}$	–	480	800	ns

**Fig. 1 - Switching Waveforms**
